

# **2018 48th European Solid-State Device Research Conference (ESSDERC 2018)**

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Time: 15:40 - 17:00

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<sup>1</sup>GLOBALFOUNDRIES, Singapore; <sup>1</sup>GLOBALFOUNDRIES, Germany; <sup>2</sup>University of Waterloo, Canada

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<sup>1</sup>*CEA-Leti, France*; <sup>2</sup>*IMEP-LAHC, France*; <sup>3</sup>*IMEP-LAHC, INPG - Minatec, France*;  
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<sup>1</sup>*Delft University of Technology, Netherlands*; <sup>2</sup>*University of California, Berkeley, United States*

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<sup>1</sup>GLOBALFOUNDRIES, Germany; <sup>2</sup>GLOBALFOUNDRIES LLC & Co. KG, Germany

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